TITLE: DEAPRON AND TRANSISTOR WITH GALLIUM NITRIDE OR GALLIUM ALUMINUM NITRIDE GATE.

INVENTORS NAME: Leonard Forbes et al.

DOCKET NO.: 303.355US4

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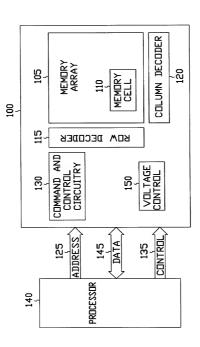


FIG. 1

TITLE: DEAPROM AND TRANSISTOR WITH GALLIUM NITRIDE OR GALLIUM ALUMINUM NITRIDE

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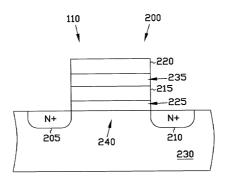


FIG. 2

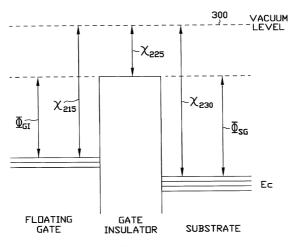


FIG. 3

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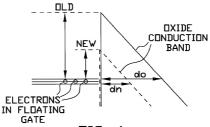


FIG. 4

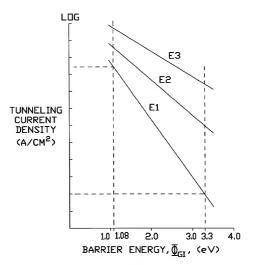


FIG. 5

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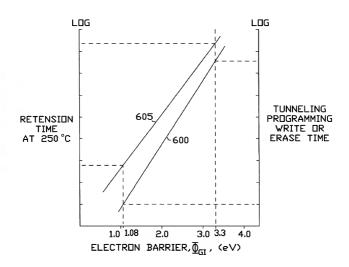
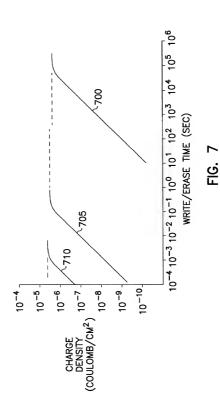


FIG. 6





TITLE: DEAPROM AND TRANSISTOR WITH GALLIUM NITRIDE OR GALLIUM ALUMINUM NITRIDE
GATE
INVENTORS NAME: Leonard Forbes et al.
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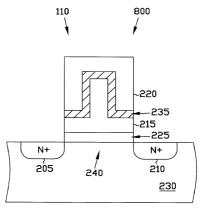


FIG. 8

and the second

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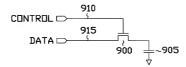


FIG. 9A (PRIDR ART)

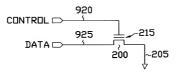


FIG. 9B

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